PTO/SB/08A ed for use through 19/31/99. OMB 0651-0031 and Trademark Office: U.S. DEPARTMENT OF COMMERCE COMPLETE IF KNOWN Substitute for form 1449A/PTO Application Number 09/018,783 **INFORMATION DISCLOSURE** Confirmation Number 1242 STATEMENT BY APPLICANT Filing Date 2/4/98 (use as many sheets as necessary) First Named Inventor Ritzdorf Group Art Unit 2823 Examiner Name Deven M. Collins Sheet 1 of 3 Attorney Docket No. 29195.8162US U.S. PATENT DOCUMENTS *EXAMINER U.S. Patent Document Cite Pages, Cohmus, Lines, Name of Patentee or Applicant Date of Publication of Cited No. INITIALS NUMBER Kind Code Where Relevant Passages or of Cited Document (if known) Document Relevant Figures Appear ÓΝ 5,972,192 Dubin et al. 10/26/99 AΒ 4,250,004 Miles et al. 2/10/81 AC 3,894,918 Corby et al 7/15/75 AD 2,443,599 Allan E. Chester 6/22/48 ΑĒ 5,605,615 Goolsby et al. 2/25/97 AF 6,280,183 Mayur et al. 8/28/01 0~ AG 6,278,089 Young et al. 8/21/01 FOREIGN PATENT DOCUMENTS *EXAMINER Cite Foreign Patent Document Pages, Columns, Lines, Where Name of Patentee or Applicant Date of Publication of INITIALS Kind Code Relevant Passages or Relevant T of Cited Document Office Cited Document Number (if known) Figures Appear OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS *EXAMINER include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, INITIALS No. journal, serial, symposium, catalog, etc.), date, page(s), volume0issue number(s), publisher, city and/or country where published NGUYEN et al. "Interconnect and Contact Metallization", Eds. H.S. Rathore, G.S. Mathan, C. Plougonver and C.C. Schuckert. PV 97-31, The Electrochemical Society, Inc., Pennington, NJ September 1997 ON ΑĦ FOULKE, D.G., in "Gold Plating Technology", Reid, F.H. and Goldic, W., p.67, Electrochemical Publication Limited, British Isles (1996). AI TOMOV, V., STOYCHEV, D.S., VITANOVA, I.B., "Recovery And Recrystallization Of Electrodeposited Bright Copper Coatings At Room Temperature. II. X-Ray Investigation Of Primary Recrystallization.", Journal ΑJ of Applied Electrochemistry, 15, 887-894. Chapman and Hall Ltd. (1985) RITZDORF, T., GRAHAM, L., JIN, S., MU, C. and FRASER, D., "Self-Annealing of Electrochemically Deposited Copper Films in Advanced Interconnect Applications," Proceedings of the IEEE 1998 International AK` Interconnect Technology Conference, San Francisco, CA (June 1-3, 1998). DUBIN, V.M., SHACHAM-DIAMAND, Y., ZHAO, B., VASUDEV, P.K. and TING, C.H., "Sub-Half Microst Electroless Cu Metallization." Materials Research Society Symposium Proceedings, Vol. 427, San Francisco ΑĪ. COOK, M. and RICHARDS, T., "The Self-Annealing of Copper," J. Inst. Metals, vol. LXX, pp. 159-173 02 (1943).AM